



$$\# \text{ addr pins} = \log_2 \# \text{ pins}$$

$\overline{CS}$  - chip select (active low)

$\overline{WE}$  - write enable (active low)

- Internal View
  - see handout
- The decoder selects a word line (makes it '1')
  - that selects a row of cells

#### 4.1) Large Memory Chips

e.g. 2M words  $\times$  8 bits

- a  $21 \times 2097152$  decoder would be slow

- instead arrange cells in a symmetric array ( $4096 \times 4096$ ) with 512 words / row

- see diagram on handout.

- the row addr and column addr share address pins (time multiplexed)

- first row addr is given, then the col addr
- latches save these addresses and are controlled by the Row Address Strobe ( $\overline{RAS}$ ) and Col Address Strobe ( $\overline{CAS}$ )

$$\begin{aligned} & 2^{21} \text{ words} \times 8 \text{ bits/word} \\ &= 2^{34} \text{ bit cells} \\ &= 16 \text{ M bits} \\ &= 4096 \times 4096 \text{ bits} \end{aligned}$$

- with Async DRAM, the controller is external to the memory chip

- see Async DRAM timing diagram

share  
some 12  
pins

4096 rows  $\Rightarrow \log_2(4096)$  row addr bits = 12 (A<sub>20-9</sub>)

512 cols  $\Rightarrow \log_2(512)$  col addr bits = 9 (A<sub>8-0</sub>)

#### 4.2) Fast Page Mode (FPM)

- a latch is added to the sense/write circuit, the whole row is latched

- (consecutive) words within same row can be read without re-selecting the row

- most DRAMs were asynchronous until mid-90's.

#### 4.3) Synchronous DRAM (SDRAM)

- has internal controller timed to memory bus

- programmed for burst of 1, 2, 4, 8 words

- see timing diagram for 2-word burst

- only initial col is needed

#### 4.4) Double Data Rate (DDR) SDRAM

- data is transferred on the rising & falling clock edges

#### 5) Memory Metrics

- latency: # cycles from  $\overline{RAS}$  until first word is produced (5 cycles in diagrams)

- bandwidth: volume of data per unit time

e.g. word size = 8 bytes, clock speed = 200 MHz,  
burst size = 2.

Async DRAM:

$$2 \text{ words} \times 8 \text{ bytes/word} \times 200 \text{ MHz} / 12 = 267 \text{ MB/s}$$

Async FPM DRAM:

$$2 \text{ words} \times 8 \text{ bytes/word} \times 200 \text{ MHz} / 9 = 356 \text{ MB/s}$$

SDRAM:

$$2 \text{ words} \times 8 \text{ bytes/word} \times 200 \text{ MHz} / 7 = 457 \text{ MB/s}$$

DDR SDRAM:

$$2 \text{ words} \times 8 \text{ bytes/word} \times 200 \text{ MHz} / 6 = 533 \text{ MB/s}$$

e.g. PC3-12800

- 800 MHz Clock

$$\Rightarrow 1600 \text{ MT/s} \times 8 \text{ bytes/transfer} = 12800 \text{ MB/s}$$

6) Memory Modules

- DIMM: dual inline memory module
- Several mem. chips are combined on a PCB (printed circuit board)